# NCV8660B

# Very Low $I_q$ LD0 150 mA Regulator with RESET and Delay Time Select

The NCV8660B is a precision very low Iq low dropout voltage regulator. Quiescent currents as low as 28 μA typical make it ideal for automotive applications requiring low quiescent current with or without a load. Integrated control features such as Reset and Delay Time Select make it ideal for powering microprocessors.

It is available with a fixed output voltage of 5.0 V and 3.3 V and regulates within ±2.0%.

## Features
- Fixed Output Voltage of 5 V and 3.3 V
- ±2.0% Output Voltage up to $V_{BAT}$ = 40 V
- Output Current up to 150 mA
- Microprocessor Compatible Control Functions:
  - Delay Time Select
  - RESET Output
- NCV Prefix for Automotive
  - Site and Change Control
  - AEC−Q100 Qualified
- Low Dropout Voltage
- Low Quiescent Current of 28 μA Typical
- Stable Under No Load Conditions
- Protection Features:
  - Thermal Shutdown
  - Short Circuit
- These are Pb−Free Devices

## Applications
- Automotive:
  - Body Control Module
  - Instrument and Clusters
  - Occupant Protection and Comfort
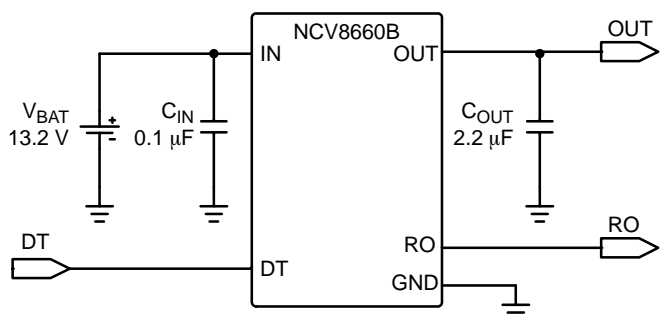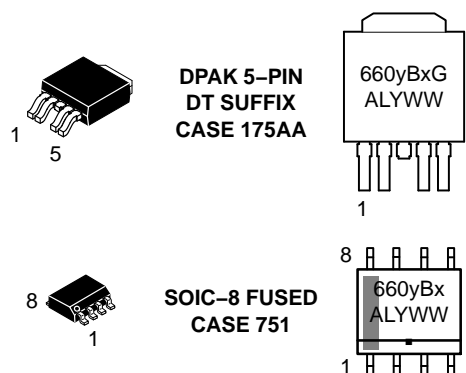  - Powertrain
- Battery Powered Consumer Electronics

**MARKING
DIAGRAMS**

DPAK 5−PIN
DT SUFFIX
CASE 175AA

```
660yBxG
ALYWW
```

SOIC−8 FUSED
CASE 751

```
660yBx
ALYWW
```

| | |
|---|---|
| x | = 5 for 5 V Output, 3 for 3.3 V Output |
| y | = 1 for 8 ms, 128 ms Reset Delay, |
| | = 2 for 8 ms, 32 ms Reset Delay |
| | = 3 for 16 ms, 64 ms Reset Delay |
| | = 4 for 32 ms, 128 ms Reset Delay |
| A | = Assembly Location |
| L | = Wafer Lot |
| Y | = Year |
| WW | = Work Week |
| G or ▪ | = Pb−Free Package |

## ORDERING INFORMATION

**Figure 1. Application Diagram**

# NCV8660B

## PIN DESCRIPTIONS

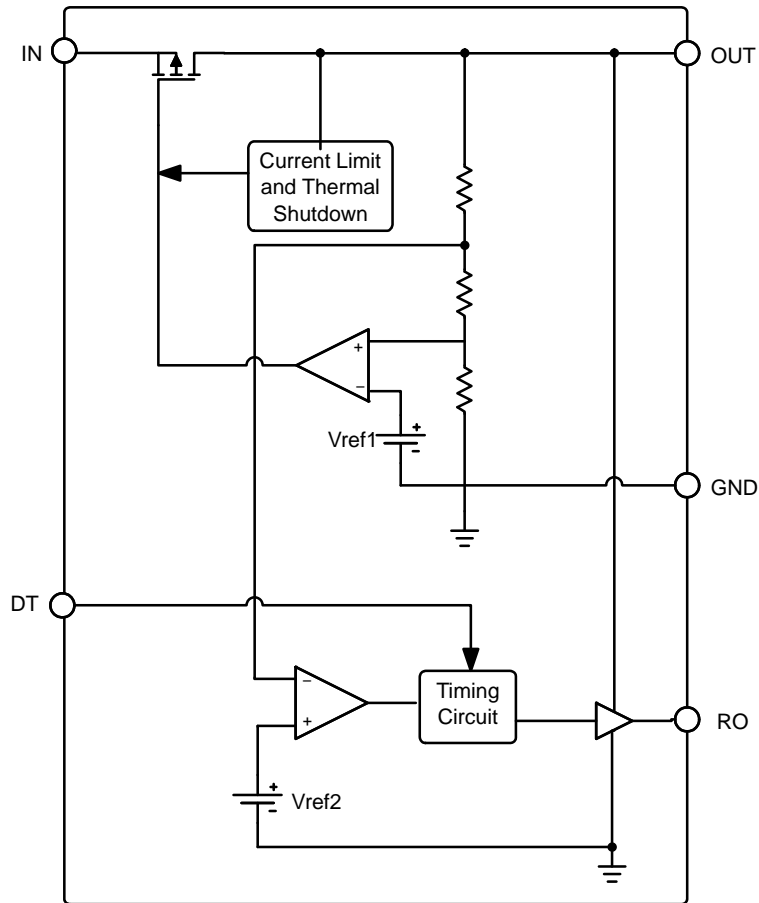| Pin | | | |
| DPAK | SOIC−8 FUSED | Symbol | Function |
| --- | --- | --- | --- |
| 1 | 1 | IN | Input Supply Voltage. 0.1 μF bypass capacitor to GND at the IC. |
| 2 | 2 | $R_O$ | Reset Output. CMOS compatible output. Goes low when $V_{OUT}$ drops by more than 7% from nominal. |
| 3, Tab | 5−8 | GND | Ground |
| 4 | 3 | DT | Reset Delay Time Select. Short to GND or connect to OUT to select time. |
| 5 | 4 | OUT | Regulated Voltage Output. 2.2 μF to ground for typical applications. |



**Figure 2. Block Diagram**

**ABSOLUTE MAXIMUM RATINGS**

| Rating | Symbol | Min | Max | Unit |
|---|---|---|---|---|
| Input Voltage (IN) | $V_{IN}$ | −0.3 | 40 | V |
| Input Current | $I_{IN}$ | −1.0 | − | mA |
| Output Voltage (OUT)<br>DC<br>Transient, t < 10 s (Note 1) | $V_{OUT}$ | −0.3<br>−0.3 | 5.5<br>16 | V |
| Output Current (OUT) | $I_{OUT}$ | −1.0 | Current Limited | mA |
| Storage Temperature Range | $T_{STG}$ | −55 | 150 | °C |
| DT (Reset Delay Time Select) Voltage (Note 2) | $V_{DT}$ | −0.3 | 16 | V |
| DT (Reset Delay Time Select) Current (Note 2) | $I_{DT}$ | −1.0 | 1.0 | mA |
| RO (Reset Output) Voltage<br>DC<br>Transient, t < 10 s | $V_{RO}$ | −0.3<br>−0.3 | 5.5<br>16 | V |
| RO (Reset Output) Current | $I_{RO}$ | −1.0 | 1.0 | mA |

**ESD CAPABILITY**

| | Symbol | Min | Max | Unit |
|---|---|---|---|---|
| ESD Capability, Human Body Model (Note 3) | $ESD_{HB}$ | −2.0 | 2.0 | kV |
| ESD Capability, Machine Model (Note 3) | $ESD_{MM}$ | −200 | 200 | V |
| ESD Capability, Charged Device Model (Note 3) | $ESD_{CDM}$ | −1.0 | 1.0 | kV |

**THERMAL RESISTANCE**

| | | Symbol | | Unit |
|---|---|---|---|---|
| Junction−to−Case (Note 4) | DPAK 5 | $R_{\theta JC}$ | 15 | °C/W |
| Junction−to−Ambient (Note 4) | DPAK 5 | $R_{\theta JA}$ | 66 | °C/W |
| Junction−to−Tab (Note 4) | DPAK 5 | $R_{\theta JT}$ | 4.0 | °C/W |
| Junction−to−Ambient (Note 4) | SOIC−8 FUSED | $R_{\theta JA}$ | 104 | °C/W |
| Junction−to−Lead (pin 6) (Note 4) | SOIC−8 FUSED | $R_{\theta JT}$ | 33 | °C/W |

**LEAD SOLDERING TEMPERATURE AND MSL**

| | | Symbol | Min | Max | Unit |
|---|---|---|---|---|---|
| Moisture Sensitivity Level | DPAK 5<br>SOIC−8 FUSED | MSL | 1<br>3 | | − |
| Lead Temperature Soldering: SMD style only, Reflow (Note 5)<br>Pb−Free Part 60 – 150 sec above 217°C, 40 sec max at peak | | SLD | − | 265 peak | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1.  The output voltage must not exceed the input voltage.
2.  External resistor required to minimize current to less than 1 mA when the control voltage is above 16 V.
3.  This device series incorporates ESD protection and is tested by the following methods:
    ESD HBM tested per AEC−Q100−002 (EIA/JESD22−A114)
    ESD MM tested per AEC−Q100−003 (EIA/JESD22−A115)
    ESD CDM tested per EIA/JESD22/C101, Field Induced Charge Model
4.  Values represented typical steady−state thermal performance on 1 oz. copper FR4 PCB with 1 $in^2$ copper area.
5.  Per IPC / JEDEC J−STD−020C.

**OPERATING RANGE**

| Pin Symbol, Parameter | Symbol | Min | Max | Unit |
|---|---|---|---|---|
| $V_{IN}$, Input Voltage Operating Range | $V_{IN}$ | 4.5 | 40 | V |
| Junction Temperature Range | $T_J$ | −40 | 150 | °C |

**ELECTRICAL CHARACTERISTICS** 5.5 V < $V_{IN}$ < 40 V, $-40°C \leq T_J \leq +150°C$, unless otherwise specified

| Characteristic | Symbol | Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **GENERAL** | | | | | | |
| Quiescent Current | $I_q$ | 100μA < $I_{OUT}$ < 150mA, $V_{IN}$ = 13.2V, $T_J$ = 25°C | – | 25 | 30 | μA |
| | | 100μA < $I_{OUT}$ < 150mA, $V_{IN}$ = 13.2V, $T_J \leq$ 85°C | – | – | 40 | |
| Thermal Shutdown (Note 6) | $T_{SD}$ | | 150 | 175 | 195 | °C |
| Thermal Hysteresis (Note 6) | $T_{HYS}$ | | – | 25 | – | °C |
| **OUT** | | | | | | |
| Output Voltage | $V_{OUT}$ | 6 V $\leq V_{IN} \leq$ 16 V, 0.1 mA $\leq I_{OUT} \leq$ 150 mA | 4.9 | 5.0 | 5.1 | V |
| | | 6 V $\leq V_{IN} \leq$ 40 V, 0.1 mA $\leq I_{OUT} \leq$ 100 mA | 4.9 | 5.0 | 5.1 | |
| | | 5.6 V $\leq V_{IN} \leq$ 16 V, 0 mA $\leq I_{OUT} \leq$ 150 mA, $-40°C \leq T_J \leq +125°C$ | 4.9 | 5.0 | 5.1 | |
| Output Voltage | $V_{OUT}$ | 5.5 V $\leq V_{IN} \leq$ 16 V, 0.1 mA $\leq I_{OUT} \leq$ 150 mA | 3.234 | 3.3 | 3.366 | V |
| | | 5.5 V $\leq V_{IN} \leq$ 40 V, 0.1 mA $\leq I_{OUT} \leq$ 100 mA | 3.234 | 3.3 | 3.366 | |
| Output Current Limit | $I_{CL}$ | OUT = 96% x $V_{OUT}$ nominal | 205 | – | 525 | mA |
| Output Current Limit, Short Circuit | $I_{SCKT}$ | OUT = 0 V | 205 | – | 525 | mA |
| Load Regulation | $\Delta V_{OUT}$ | $V_{IN}$ = 13.2 V, $I_{OUT}$ = 0.1 mA to 150 mA | –40 | 10 | 40 | mV |
| Line Regulation | $\Delta V_{OUT}$ | $I_{OUT}$ = 5 mA, $V_{IN}$ = 6 V to 28 V | –20 | 0 | 20 | mV |
| Dropout Voltage – 5.0 V Only | $V_{DR}$ | $I_{OUT}$ = 100 mA, (Note 7) $V_{DR} = V_{IN} - V_{OUT}$, ($\Delta V_{OUT}$ = –100 mV) | – | 0.225 | 0.45 | V |
| | | $I_{OUT}$ = 150 mA, (Note 7) $V_{DR} = V_{IN} - V_{OUT}$, ($\Delta V_{OUT}$ = –100 mV) | – | 0.30 | 0.60 | |
| Output Load Capacitance | $C_O$ | Output capacitance for stability | 2.2 | – | – | μF |
| Power Supply Ripple Rejection | PSRR | $V_{IN}$ = 13.2 V, 0.5 $V_{PP}$, 100 Hz | – | 60 | – | dB |
| **DT (Reset Delay Time Select)** | | | | | | |
| Threshold Voltage          High            Low | | | 2 – | – – | – 0.8 | V V |
| Input Current | | DT = $V_{OUT}$ | – | – | 1.0 | μA |
| **RO, Reset Output** | | | | | | |
| RESET Threshold | $V_{Rf}$ | $V_{OUT}$ decreasing | 90 | 93 | 96 | %$V_{OUT}$ |
| RESET Threshold Hysteresis | $V_{Rhys}$ | | – | 2.0 | – | %$V_{OUT}$ |
| RO Output Low | $V_{RL}$ | 10 kΩ RESET to OUT, $V_{OUT}$ = 4.5 V | – | 0.2 | 0.4 | V |
| RO Output High (OUT–RO) | $V_{RH}$ | 10 kΩ RESET to GND | $V_{OUT}$ –0.4 | $V_{OUT}$ –0.2 | $V_{OUT}$ | V |
| Reset Reaction Time | $t_{RR}$ | $V_{OUT}$ into UV to RESET Low | 16 | 25 | 38 | μsec |
| Input Voltage Reset Threshold | $V_{IN\_RT}$ | $V_{IN}$ Decreasing, $V_{OUT} > V_{RT}$ | – | 3.8 | 4.25 | V |
| **RESET Delay with DT Selection** | | | | | | |
| Delay Time Out of RESET<br>– 8 ms version<br>– 16 ms version<br>– 32 ms version<br>– 64 ms version<br>– 128 ms version | $t_{dRx}$ | $V_{OUT}$ into regulation to RO High | 5.0<br>10<br>20<br>40<br>80 | 8.0<br>16<br>32<br>64<br>128 | 11.5<br>23<br>46<br>92<br>184 | msec |

6. Not production tested, guaranteed by design.
7. Dropout at a given current level is defined as the voltage difference of $V_{IN}$ to $V_{OUT}$ with $V_{IN}$ decreasing until the output drops by 100 mV.
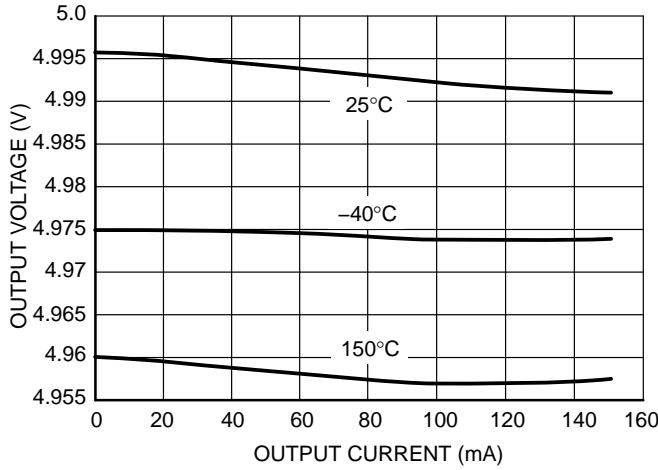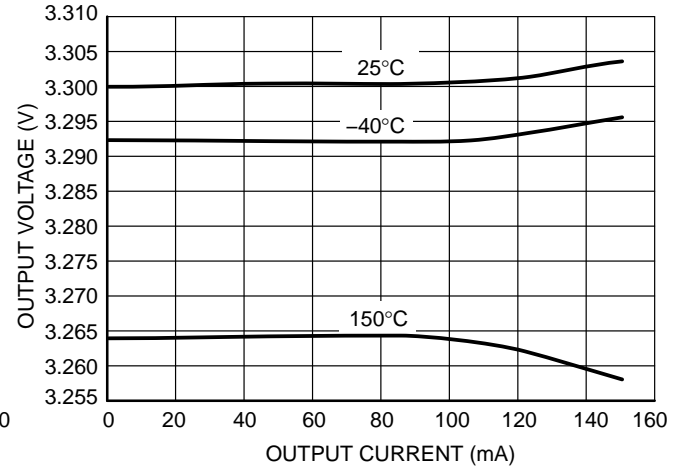
## TYPICAL OPERATING CHARACTERISTICS
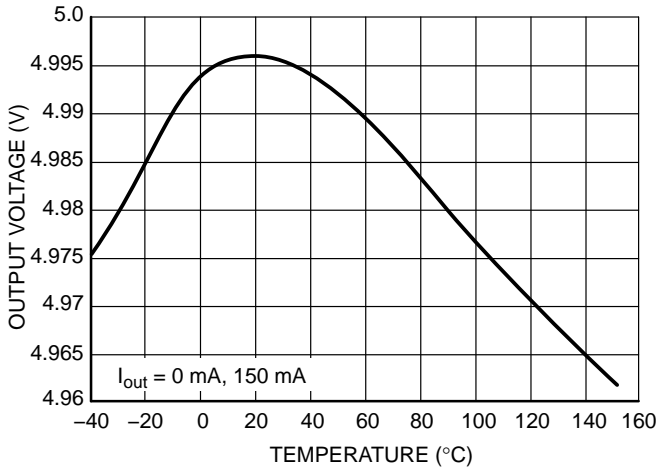


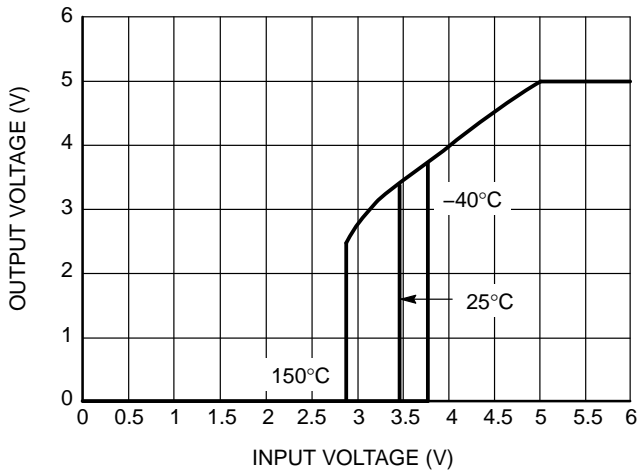**Figure 3. Output Voltage vs. Temperature (OUT = 5 V)**
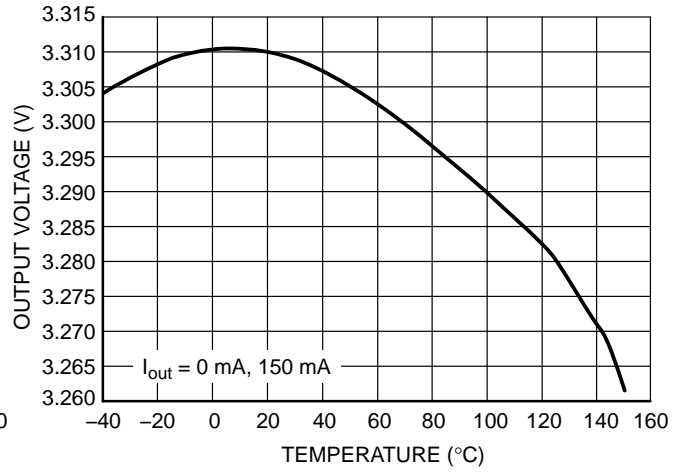


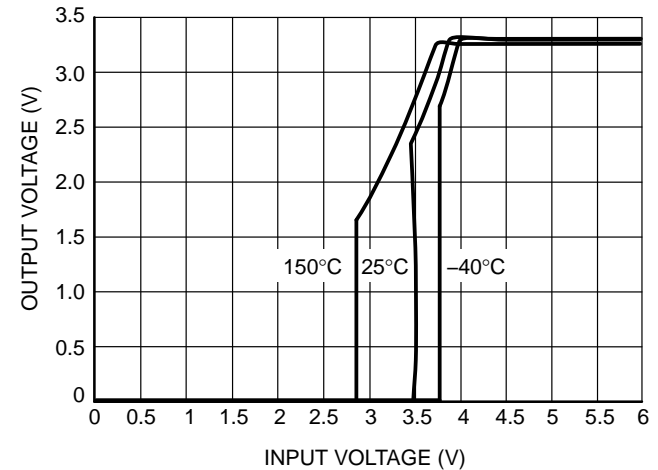**Figure 4. Output Voltage vs. Temperature (OUT = 3.3 V)**



**Figure 5. Output Voltage vs. Output Current (OUT = 5 V)**



**Figure 6. Output Voltage vs. Output Current (OUT = 3.3 V)**



**Figure 7. Output Voltage vs. Input Voltage ($R_{LOAD}$ = 51 k, $I_{out}$ = 100 μA, OUT = 5 V)**



**Figure 8. Output Voltage vs. Input Voltage ($R_{LOAD}$ = 33 k, $I_{out}$ = 100 μA, OUT = 3.3 V)**

## TYPICAL OPERATING CHARACTERISTICS
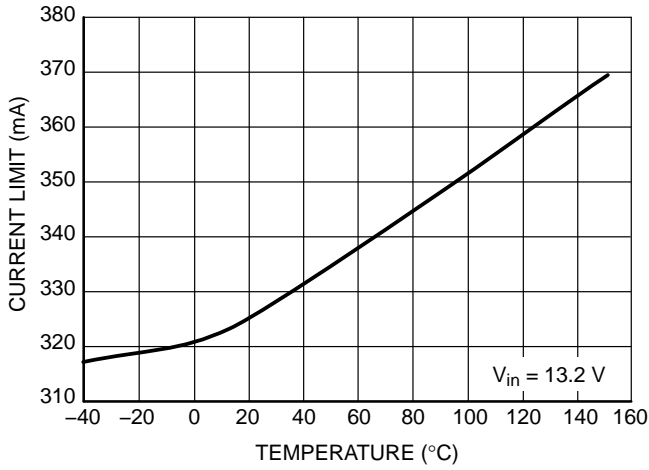


**Figure 9. Current Limit vs. Temperature**
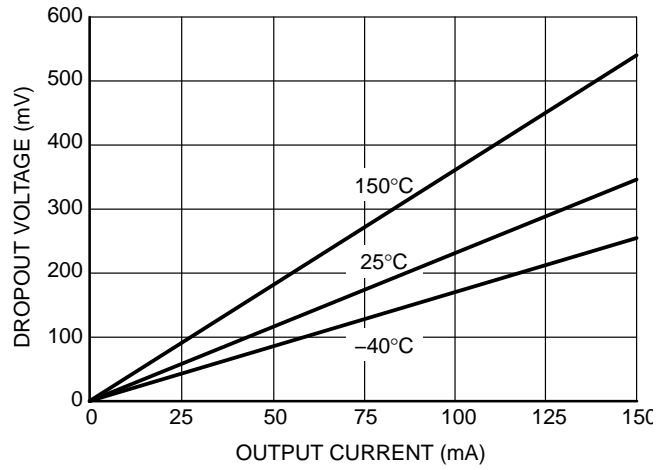


**Figure 10. Dropout Voltage vs. Output Current**
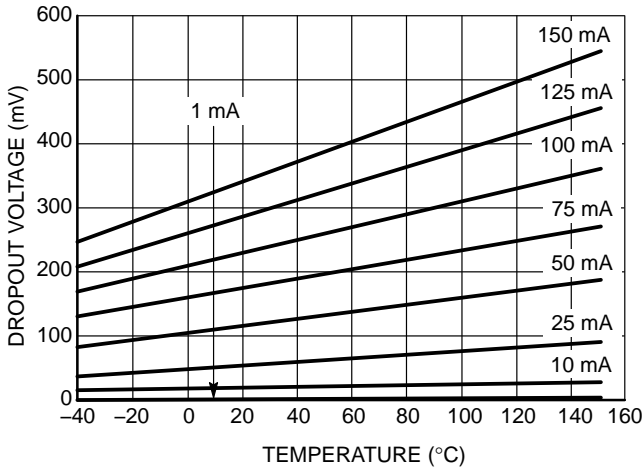


**Figure 11. Dropout Voltage vs. Temperature**
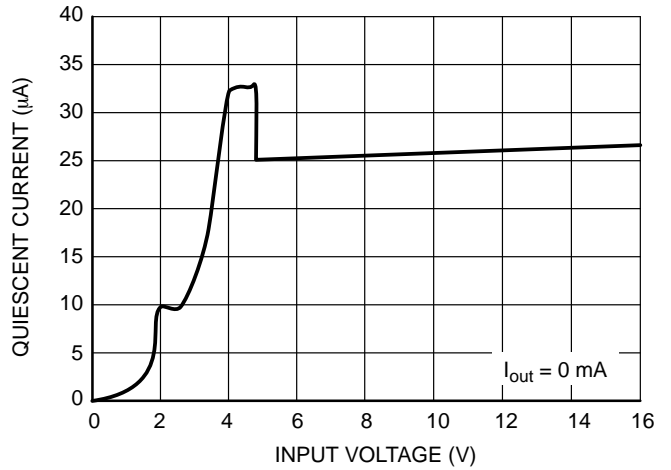


**Figure 12. Quiescent Current vs. Input Voltage**
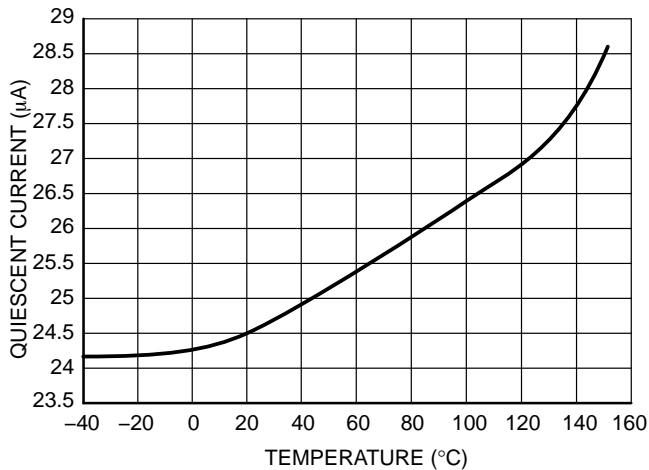


**Figure 13. Quiescent Current vs. Temperature**
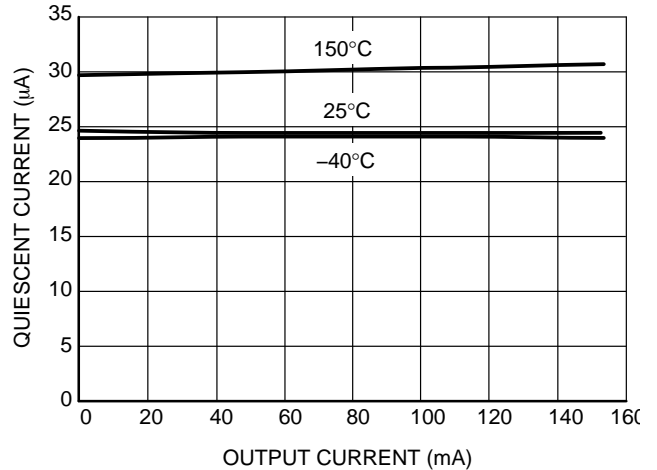


**Figure 14. Quiescent Current vs. Output Current**

## TYPICAL OPERATING CHARACTERISTICS
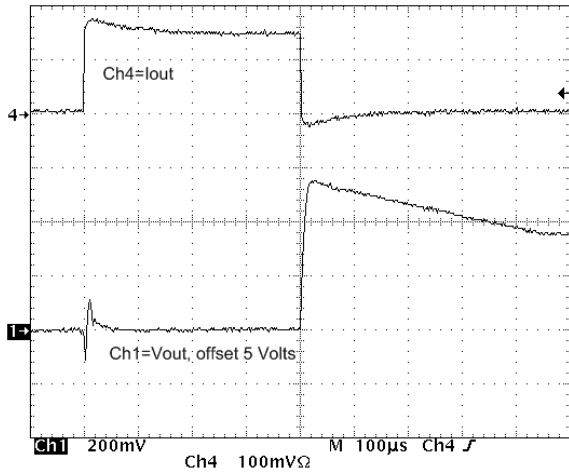
**Figure 15. Load Transient**
**(V$_{IN}$ = 13.2 V, OUT = 5 V)**
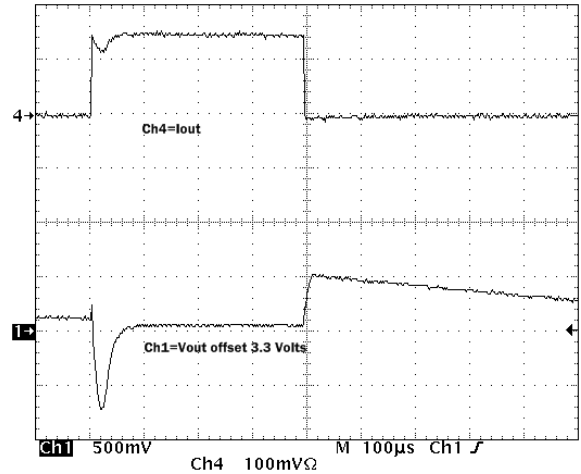
**Figure 17. Load Transient**
**(V$_{IN}$ = 13.2 V, OUT = 3.3 V)**
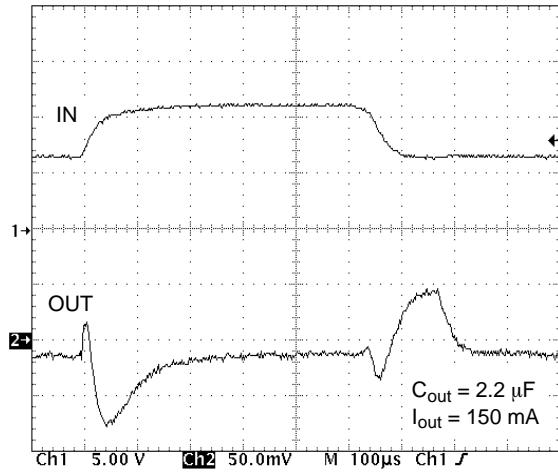
**Figure 16. Line Transient (OUT = 5 V)**
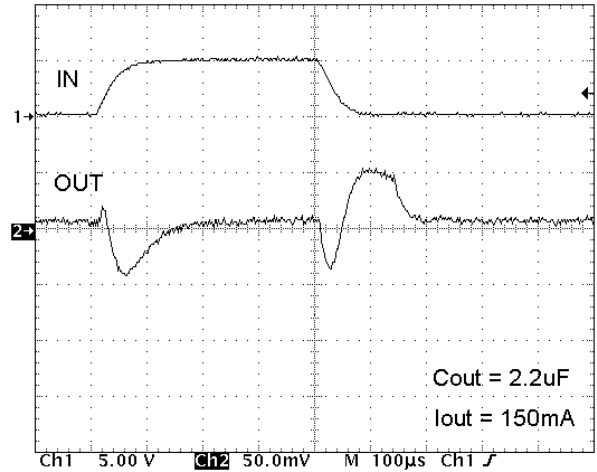
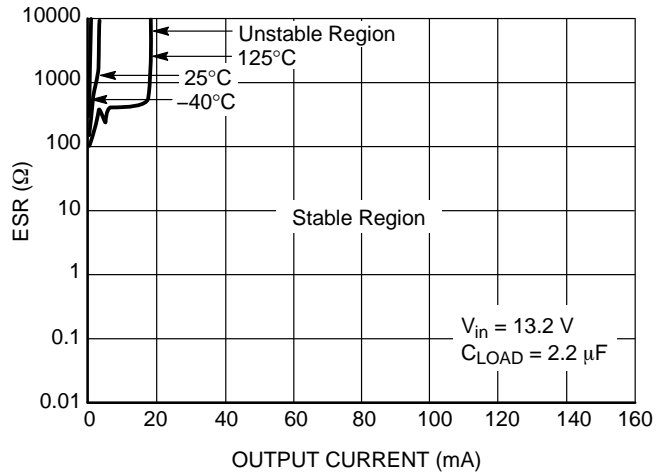**Figure 18. Line Transient (OUT = 3.3 V)**

## TYPICAL OPERATING CHARACTERISTICS
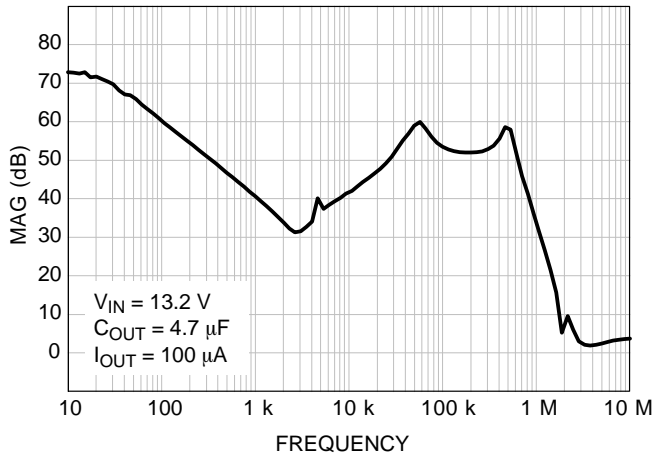
**Figure 19. Ripple Rejection vs. Frequency**
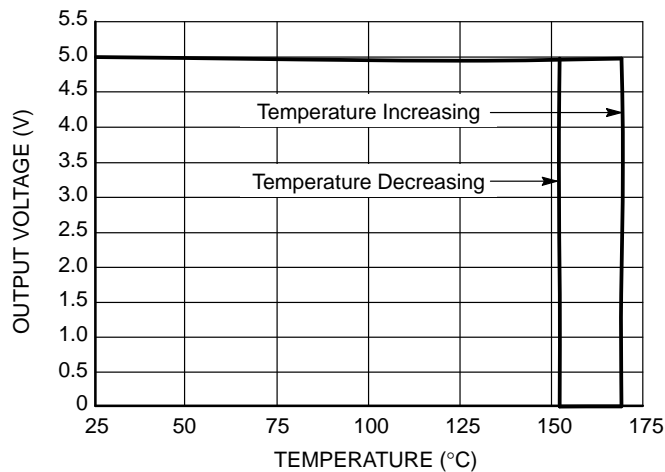**($V_{IN}$ = 13.2 V, $I_{OUT}$ = 100 μA)**
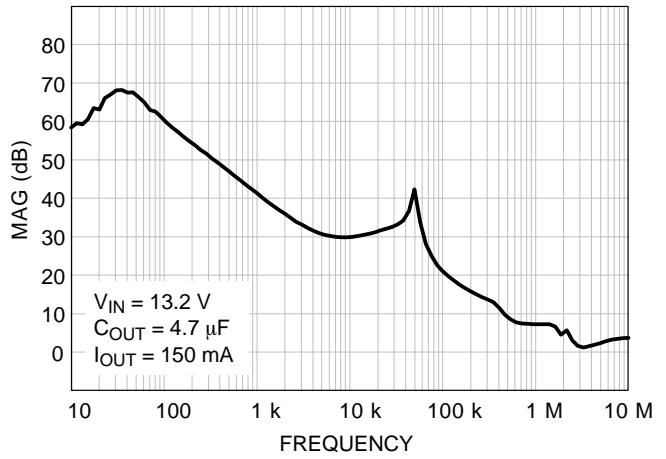
**Figure 20. Ripple Rejection vs. Frequency**
**($V_{IN}$ = 13.2 V, $I_{OUT}$ = 150 mA)**
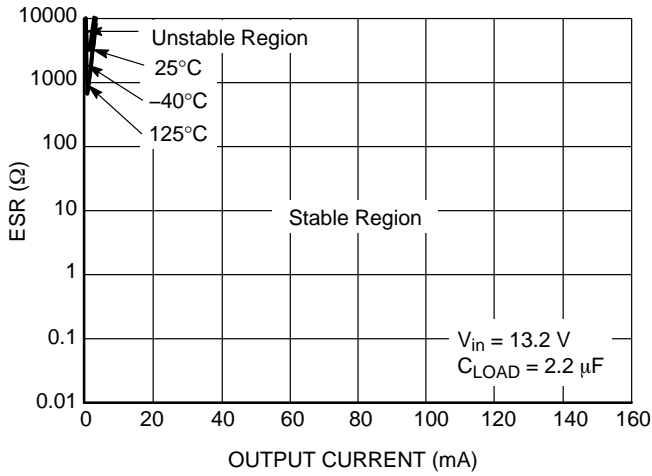
**Figure 21. Output Capacitor ESR vs. Output Current (OUT = 5 V)**

**Figure 22. Output Capacitor ESR vs. Output Current (OUT = 3.3 V)**

**Figure 23. Thermal Shutdown vs. Temperature**

## DETAILED OPERATING DESCRIPTION

### General

The NCV8660B is a 5 V and 3.3 V linear regulator providing low drop–out voltage for 150 mA at low quiescent current levels. Also featured in this part is a reset output with selectable delay times. Delay times are selectable via part selection and control through the Delay Time Select (DT) pin. No pull–up resistor is needed on the reset output (RO). Pull–up and pull–down capability are included. Only a small bypass capacitor on the input (IN) supply pin and output (OUT) voltage pin are required for normal operation. Thermal shutdown functionality protects the IC from damage caused from excessively high temperatures appearing on the IC.

### Output Voltage

Output stability is determined by the capacitor selected from OUT to GND. The NCV8660B has been designed to work with low ESR (equivalent series resistance) ceramic capacitors. The device is extremely stable using virtually any capacitor 2.2 μF and above. Reference the Output Capacitor Stability graph in Figure 21.

The output capacitor value will affect overshoot during power–up. A lower value capacitor will cause higher overshoot on the output. System evaluation should be performed with minimum loading for evaluation of overshoot.

Selection of process technology for the NCV8660B allows for low quiescent current independent of loading. Quiescent current will remain flat across the entire range of loads providing a low quiescent current condition in standby and under heavy loads. This is highly beneficial to systems requiring microprocessor interrupts during standby mode as duty cycle and load changes have no impact on the standby current. Reference Figure 14 for Quiescent Current vs Output Current.

### Current Limit

Current limit is provided on OUT to protect the IC. The minimum specification is 205 mA. Current limit is specified under two conditions (OUT = 96% x OUT nominal) and (OUT = 0 V). No fold–back circuitry exists. Any measured differences can be attributed to change in die temperature. The part may be operated up to 205 mA provided thermal die temperature is considered and is kept below 150°C. Degradation of electrical parameters at this current is expected at these elevated levels. A reset (RO) will not occur with a load less than 205 mA.

### Reset Output

A reset signal is provided on the Reset Output (RO) pin to provide feedback to the microprocessor of an out of regulation condition. This is in the form of a logic signal on RO. Output (OUT) voltage conditions below the RESET threshold cause RO to go low. The RO integrity is maintained down to OUT = 1.0 V.

The Reset Output (RO) circuitry includes an active internal pullup to the output (OUT) as shown in Figure 24. No external pullup is neccessary.
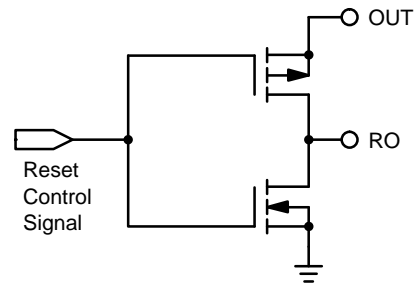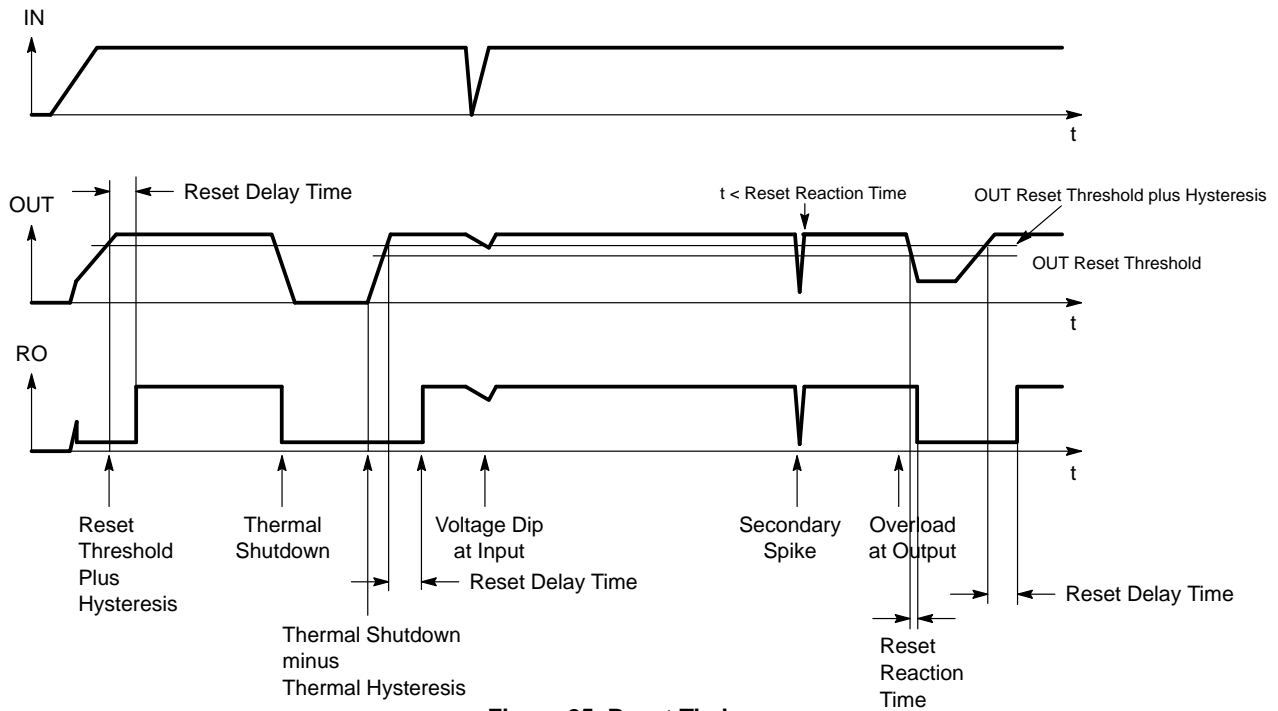


**Figure 24. Reset Output Circuitry**

**Figure 25. Reset Timing**

During power−up (or restoring OUT voltage from a reset event), the OUT voltage must be maintained above the Reset threshold for the Reset Delay time before RO goes high. The time for Reset Delay is determined by the choice of IC and the state of the DT pin.

**Reset Delay Time Select**

Selection of the NCV8660B device and the state of the DT pin determines the available Reset Delay times. The part is designed for use with DT tied to ground or OUT, but may be controlled by any logic signal which provides a threshold between 0.8 V and 2 V. The default condition for an open DT pin is the slower Reset time (DT = GND condition). Times are in pairs and are highlighted in the chart below. Consult factory for availability.

| | DT=GND | DT=OUT |
|---|---|---|
| | **Reset Time** | **Reset Time** |
| NCV86601B | 8 ms | 128 ms |
| NCV86602B | 8 ms | 32 ms |
| NCV86603B | 16 ms | 64 ms |
| NCV86604B | 32 ms | 128 ms |

The Delay Time select (DT) pin is logic level controlled and provides Reset Delay time per the chart. Note the DT pin is sampled only when RO is low, and changes to the DT pin when RO is high will not effect the reset delay time.

**Thermal Shutdown**

When the die temperature exceeds the Thermal Shutdown threshold, a Thermal Shutdown event is detected OUT is turned off, and RO goes low. The IC will remain in this state until the die temperature moves below the shutdown threshold (175°C typical) minus the hysteresis factor (25°C typical). The output will then turn back on and RO will go high after the RESET Delay time.
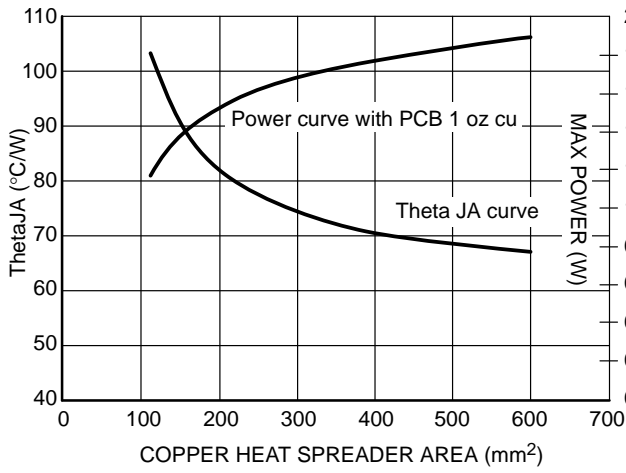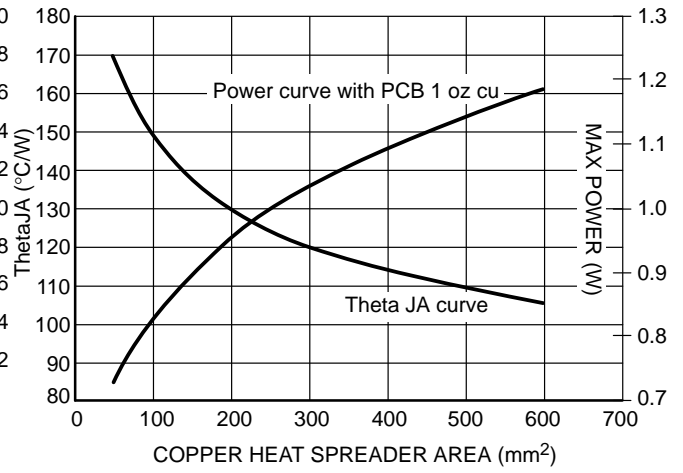
**Figure 26. R$_{\theta JA}$ vs. PCB Copper Area (DPAK)**



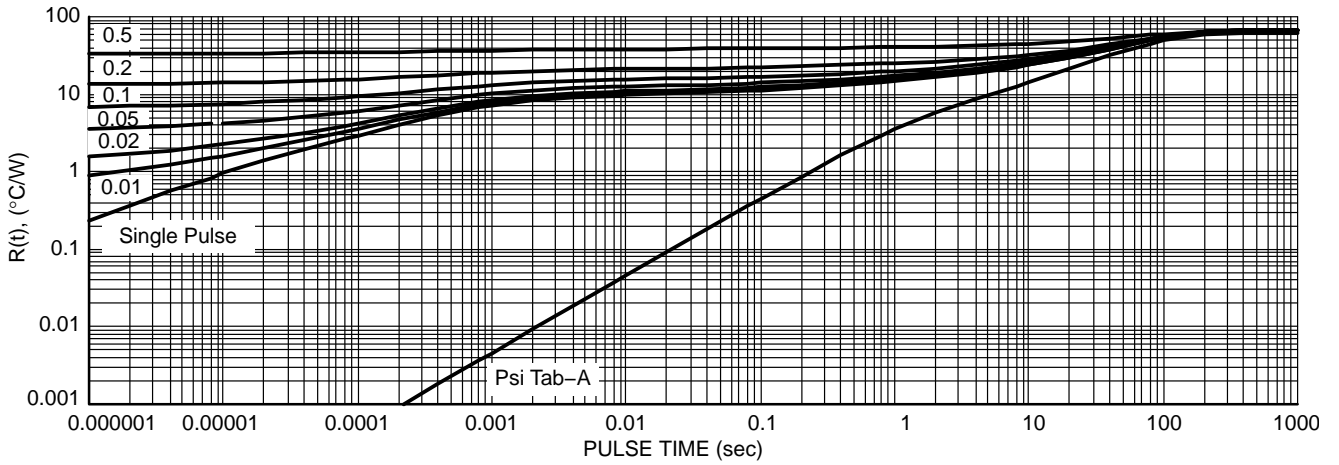**Figure 28. R$_{\theta JA}$ vs. PCB Copper Area (SOIC−8 Fused)**



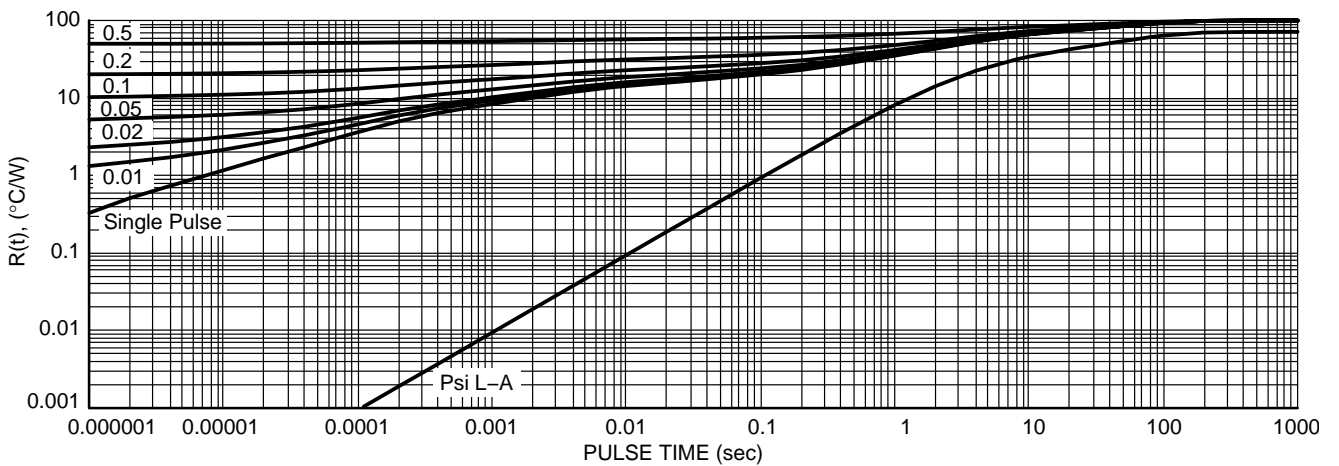**Figure 27. Transient Thermal Response (DPAK)**
**Cu Area = 645 mm$^2$**



**Figure 29. Transient Thermal Response (SOIC−8 Fused)**
**Cu Area = 645 mm$^2$**

# NCV8660B

## ORDERING INFORMATION

| Device | Output Voltage | Reset Delay Time, DT to GND | Reset Delay Time, DT to OUT | Package | Shipping[†] |
|---|---|---|---|---|---|
| NCV86601BDT50RKG | 5.0 V | 8 ms | 128 ms | DPAK (Pb−Free) | 2500 / Tape & Reel |
| NCV86602BDT50RKG | | 8 ms | 32 ms | | |
| NCV86603BDT50RKG | | 16 ms | 64 ms | | |
| NCV86604BDT50RKG | | 32 ms | 128 ms | | |
| NCV86601BD50R2G | | 8 ms | 128 ms | SOIC−8 FUSED (Pb−Free) | 2500 / Tape & Reel |
| NCV86602BD50R2G | | 8 ms | 32 ms | | |
| NCV86603BD50R2G | | 16 ms | 64 ms | | |
| NCV86604BD50R2G | | 32 ms | 128 ms | | |
| NCV86601BDT33RKG | 3.3 V | 8 ms | 128 ms | DPAK (Pb−Free) | 2500 / Tape & Reel |
| NCV86602BDT33RKG | | 8 ms | 32 ms | | |
| NCV86603BDT33RKG | | 16 ms | 64 ms | | |
| NCV86604BDT33RKG | | 32 ms | 128 ms | | |
| NCV86601BD33R2G | | 8 ms | 128 ms | SOIC−8 FUSED (Pb−Free) | 2500 / Tape & Reel |
| NCV86602BD33R2G | | 8 ms | 32 ms | | |
| NCV86603BD33R2G | | 16 ms | 64 ms | | |
| NCV86604BD33R2G | | 32 ms | 128 ms | | |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NCV8660B

## PACKAGE DIMENSIONS

**DPAK 5, CENTER LEAD CROP**
CASE 175AA
ISSUE B
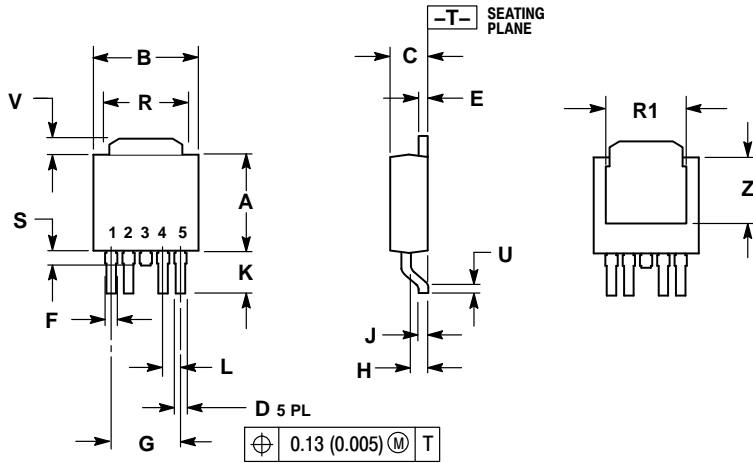
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|--------|-------------|--------|
| | MIN | MAX | MIN | MAX |
| A | 0.235 | 0.245 | 5.97 | 6.22 |
| B | 0.250 | 0.265 | 6.35 | 6.73 |
| C | 0.086 | 0.094 | 2.19 | 2.38 |
| D | 0.020 | 0.028 | 0.51 | 0.71 |
| E | 0.018 | 0.023 | 0.46 | 0.58 |
| F | 0.024 | 0.032 | 0.61 | 0.81 |
| G | 0.180 BSC | | 4.56 BSC | |
| H | 0.034 | 0.040 | 0.87 | 1.01 |
| J | 0.018 | 0.023 | 0.46 | 0.58 |
| K | 0.102 | 0.114 | 2.60 | 2.89 |
| L | 0.045 BSC | | 1.14 BSC | |
| R | 0.170 | 0.190 | 4.32 | 4.83 |
| R1 | 0.185 | 0.210 | 4.70 | 5.33 |
| S | 0.025 | 0.040 | 0.63 | 1.01 |
| U | 0.020 | ––– | 0.51 | ––– |
| V | 0.035 | 0.050 | 0.89 | 1.27 |
| Z | 0.155 | 0.170 | 3.93 | 4.32 |

## SOLDERING FOOTPRINT*
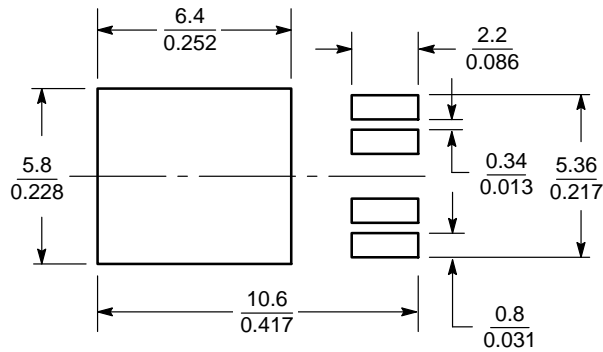
SCALE 4:1  $\left(\dfrac{mm}{inches}\right)$

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NCV8660B

## PACKAGE DIMENSIONS

**SOIC−8 NB**
CASE 751−07
ISSUE AK
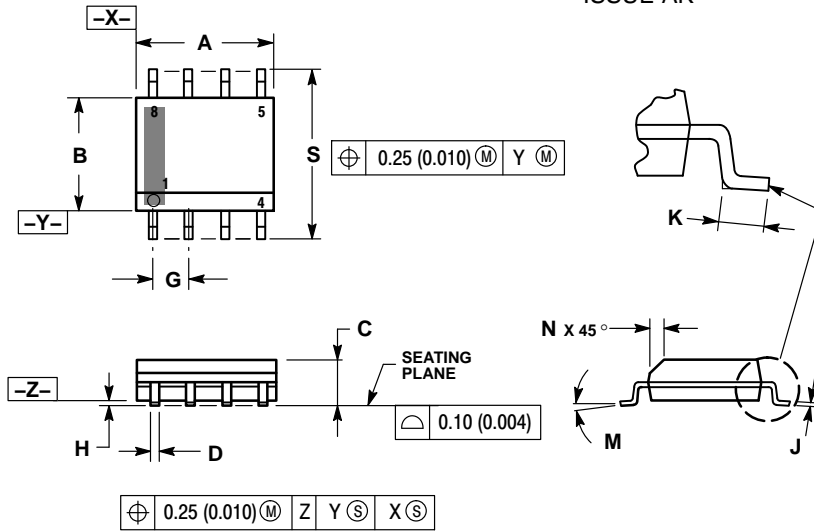


**NOTES:**
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

| DIM | MILLIMETERS | | INCHES | |
|-----|-----|-----|-----|-----|
| | **MIN** | **MAX** | **MIN** | **MAX** |
| A | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0 ° | 8 ° | 0 ° | 8 ° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

## SOLDERING FOOTPRINT*



SCALE 6:1    $\left(\dfrac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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**NCV8660B/D**